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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	832
Number of Logic Elements/Cells	8320
Total RAM Bits	106496
Number of I/O	174
Number of Gates	526000
Voltage - Supply	2.375V ~ 2.625V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	240-BFQFP
Supplier Device Package	240-PQFP (32x32)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep20k200qi240-3

Logic Array Block

Each LAB consists of 10 LEs, the LEs' associated carry and cascade chains, LAB control signals, and the local interconnect. The local interconnect transfers signals between LEs in the same or adjacent LABs, IOEs, or ESBs. The Quartus II Compiler places associated logic within an LAB or adjacent LABs, allowing the use of a fast local interconnect for high performance. Figure 3 shows the APEX 20K LAB.

APEX 20K devices use an interleaved LAB structure. This structure allows each LE to drive two local interconnect areas. This feature minimizes use of the MegaLAB and FastTrack interconnect, providing higher performance and flexibility. Each LE can drive 29 other LEs through the fast local interconnect.

Figure 3. LAB Structure

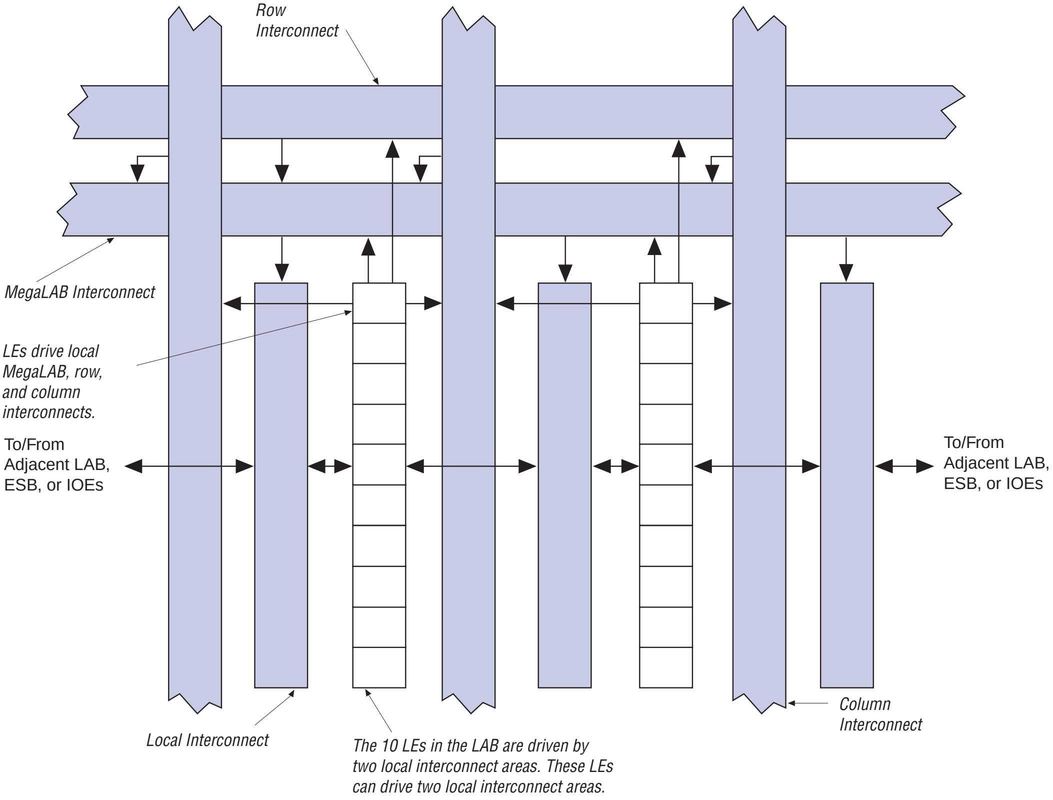
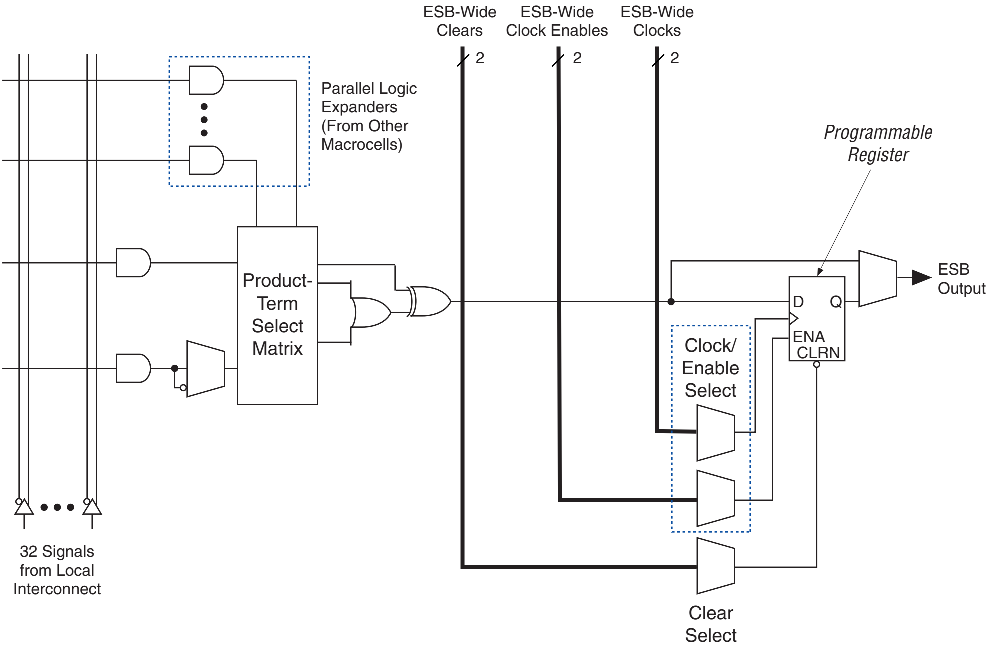


Figure 14. APEX 20K Macrocell

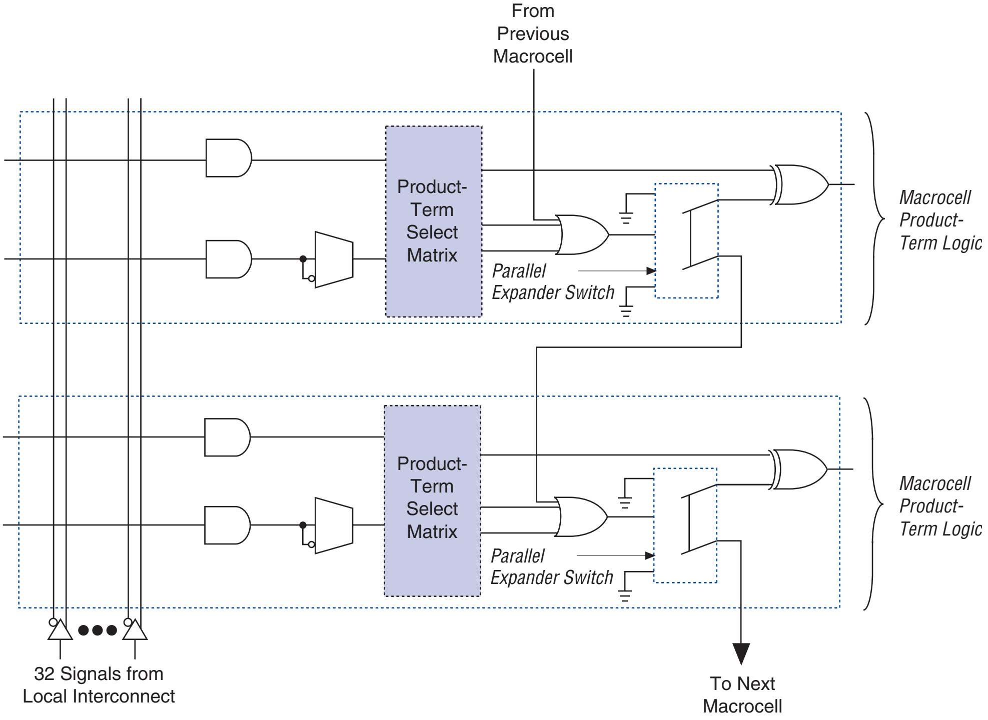


For registered functions, each macrocell register can be programmed individually to implement D, T, JK, or SR operation with programmable clock control. The register can be bypassed for combinatorial operation. During design entry, the designer specifies the desired register type; the Quartus II software then selects the most efficient register operation for each registered function to optimize resource utilization. The Quartus II software or other synthesis tools can also select the most efficient register operation automatically when synthesizing HDL designs.

Each programmable register can be clocked by one of two ESB-wide clocks. The ESB-wide clocks can be generated from device dedicated clock pins, global signals, or local interconnect. Each clock also has an associated clock enable, generated from the local interconnect. The clock and clock enable signals are related for a particular ESB; any macrocell using a clock also uses the associated clock enable.

If both the rising and falling edges of a clock are used in an ESB, both ESB-wide clock signals are used.

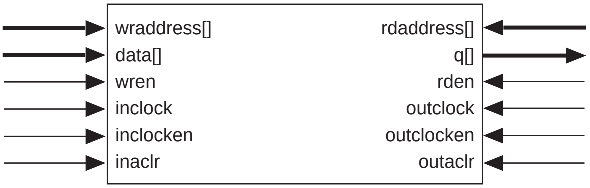
Figure 16. APEX 20K Parallel Expanders



Embedded System Block

The ESB can implement various types of memory blocks, including dual-port RAM, ROM, FIFO, and CAM blocks. The ESB includes input and output registers; the input registers synchronize writes, and the output registers can pipeline designs to improve system performance. The ESB offers a dual-port mode, which supports simultaneous reads and writes at two different clock frequencies. Figure 17 shows the ESB block diagram.

Figure 17. ESB Block Diagram



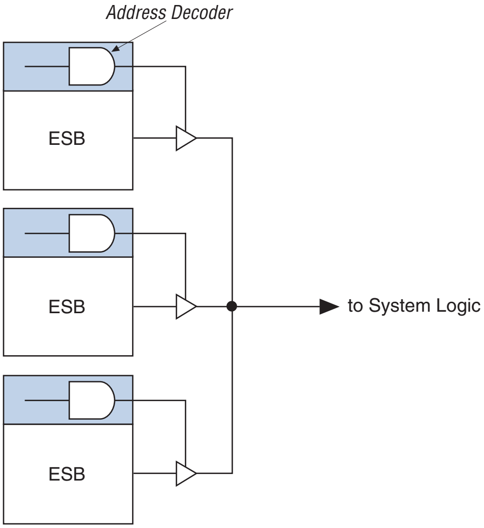
ESBs can implement synchronous RAM, which is easier to use than asynchronous RAM. A circuit using asynchronous RAM must generate the RAM write enable (`WE`) signal, while ensuring that its data and address signals meet setup and hold time specifications relative to the `WE` signal. In contrast, the ESB's synchronous RAM generates its own `WE` signal and is self-timed with respect to the global clock. Circuits using the ESB's self-timed RAM must only meet the setup and hold time specifications of the global clock.

ESB inputs are driven by the adjacent local interconnect, which in turn can be driven by the MegaLAB or FastTrack Interconnect. Because the ESB can be driven by the local interconnect, an adjacent LE can drive it directly for fast memory access. ESB outputs drive the MegaLAB and FastTrack Interconnect. In addition, ten ESB outputs, nine of which are unique output lines, drive the local interconnect for fast connection to adjacent LEs or for fast feedback product-term logic.

When implementing memory, each ESB can be configured in any of the following sizes: 128 × 16, 256 × 8, 512 × 4, 1,024 × 2, or 2,048 × 1. By combining multiple ESBs, the Quartus II software implements larger memory blocks automatically. For example, two 128 × 16 RAM blocks can be combined to form a 128 × 32 RAM block, and two 512 × 4 RAM blocks can be combined to form a 512 × 8 RAM block. Memory performance does not degrade for memory blocks up to 2,048 words deep. Each ESB can implement a 2,048-word-deep memory; the ESBs are used in parallel, eliminating the need for any external control logic and its associated delays.

To create a high-speed memory block that is more than 2,048 words deep, ESBs drive tri-state lines. Each tri-state line connects all ESBs in a column of MegaLAB structures, and drives the MegaLAB interconnect and row and column FastTrack Interconnect throughout the column. Each ESB incorporates a programmable decoder to activate the tri-state driver appropriately. For instance, to implement 8,192-word-deep memory, four ESBs are used. Eleven address lines drive the ESB memory, and two more drive the tri-state decoder. Depending on which 2,048-word memory page is selected, the appropriate ESB driver is turned on, driving the output to the tri-state line. The Quartus II software automatically combines ESBs with tri-state lines to form deeper memory blocks. The internal tri-state control logic is designed to avoid internal contention and floating lines. See Figure 18.

Figure 18. Deep Memory Block Implemented with Multiple ESBs



The ESB implements two forms of dual-port memory: read/write clock mode and input/output clock mode. The ESB can also be used for bidirectional, dual-port memory applications in which two ports read or write simultaneously. To implement this type of dual-port memory, two or four ESBs are used to support two simultaneous reads or writes. This functionality is shown in Figure 19.

Figure 19. APEX 20K ESB Implementing Dual-Port RAM

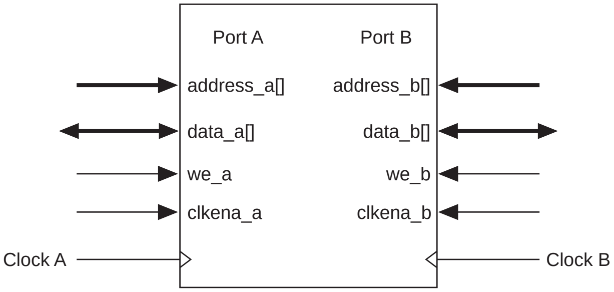
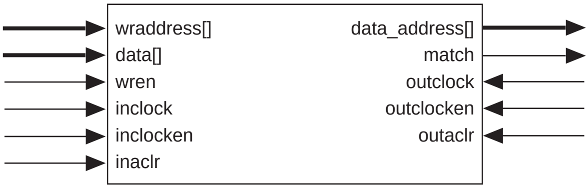


Figure 23. APEX 20KE CAM Block Diagram



CAM can be used in any application requiring high-speed searches, such as networking, communications, data compression, and cache management.

The APEX 20KE on-chip CAM provides faster system performance than traditional discrete CAM. Integrating CAM and logic into the APEX 20KE device eliminates off-chip and on-chip delays, improving system performance.

When in CAM mode, the ESB implements 32-word, 32-bit CAM. Wider or deeper CAM can be implemented by combining multiple CAMs with some ancillary logic implemented in LEs. The Quartus II software combines ESBs and LEs automatically to create larger CAMs.

CAM supports writing "don't care" bits into words of the memory. The "don't-care" bit can be used as a mask for CAM comparisons; any bit set to "don't-care" has no effect on matches.

The output of the CAM can be encoded or unencoded. When encoded, the ESB outputs an encoded address of the data's location. For instance, if the data is located in address `12`, the ESB output is `12`. When unencoded, the ESB uses its 16 outputs to show the location of the data over two clock cycles. In this case, if the data is located in address `12`, the 12th output line goes high. When using unencoded outputs, two clock cycles are required to read the output because a 16-bit output bus is used to show the status of 32 words.

The encoded output is better suited for designs that ensure duplicate data is not written into the CAM. If duplicate data is written into two locations, the CAM's output will be incorrect. If the CAM may contain duplicate data, the unencoded output is a better solution; CAM with unencoded outputs can distinguish multiple data locations.

CAM can be pre-loaded with data during configuration, or it can be written during system operation. In most cases, two clock cycles are required to write each word into CAM. When "don't-care" bits are used, a third clock cycle is required.

Advanced I/O Standard Support

APEX 20KE IOEs support the following I/O standards: LVTTL, LVCMOS, 1.8-V I/O, 2.5-V I/O, 3.3-V PCI, PCI-X, 3.3-V AGP, LVDS, LVPECL, GTL+, CTT, HSTL Class I, SSTL-3 Class I and II, and SSTL-2 Class I and II.

For more information on I/O standards supported by APEX 20KE devices, see *Application Note 117 (Using Selectable I/O Standards in Altera Devices)*.

The APEX 20KE device contains eight I/O banks. In QFP packages, the banks are linked to form four I/O banks. The I/O banks directly support all standards except LVDS and LVPECL. All I/O banks can support LVDS and LVPECL with the addition of external resistors. In addition, one block within a bank contains circuitry to support high-speed True-LVDS and LVPECL inputs, and another block within a particular bank supports high-speed True-LVDS and LVPECL outputs. The LVDS blocks support all of the I/O standards. Each I/O bank has its own `VCCIO` pins. A single device can support 1.8-V, 2.5-V, and 3.3-V interfaces; each bank can support a different standard independently. Each bank can also use a separate V_{REF} level so that each bank can support any of the terminated standards (such as SSTL-3) independently. Within a bank, any one of the terminated standards can be supported. EP20K300E and larger APEX 20KE devices support the LVDS interface for data pins (smaller devices support LVDS clock pins, but not data pins). All EP20K300E and larger devices support the LVDS interface for data pins up to 155 Mbit per channel; EP20K400E devices and larger with an X-suffix on the ordering code add a serializer/deserializer circuit and PLL for higher-speed support.

Each bank can support multiple standards with the same `VCCIO` for output pins. Each bank can support one voltage-referenced I/O standard, but it can support multiple I/O standards with the same `VCCIO` voltage level. For example, when `VCCIO` is 3.3 V, a bank can support LVTTL, LVCMOS, 3.3-V PCI, and SSTL-3 for inputs and outputs.

When the LVDS banks are not used as LVDS I/O banks, they support all of the other I/O standards. Figure 29 shows the arrangement of the APEX 20KE I/O banks.

Clock Phase & Delay Adjustment

The APEX 20KE ClockShift feature allows the clock phase and delay to be adjusted. The clock phase can be adjusted by 90° steps. The clock delay can be adjusted to increase or decrease the clock delay by an arbitrary amount, up to one clock period.

LVDS Support

Two PLLs are designed to support the LVDS interface. When using LVDS, the I/O clock runs at a slower rate than the data transfer rate. Thus, PLLs are used to multiply the I/O clock internally to capture the LVDS data. For example, an I/O clock may run at 105 MHz to support 840 megabits per second (Mbps) LVDS data transfer. In this example, the PLL multiplies the incoming clock by eight to support the high-speed data transfer. You can use PLLs in EP20K400E and larger devices for high-speed LVDS interfacing.

Lock Signals

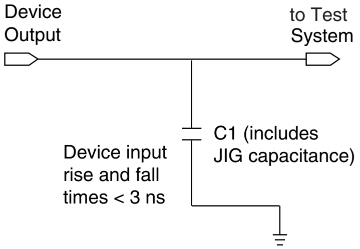
The APEX 20KE ClockLock circuitry supports individual `LOCK` signals. The `LOCK` signal drives high when the ClockLock circuit has locked onto the input clock. The `LOCK` signals are optional for each ClockLock circuit; when not used, they are I/O pins.

ClockLock & ClockBoost Timing Parameters

For the ClockLock and ClockBoost circuitry to function properly, the incoming clock must meet certain requirements. If these specifications are not met, the circuitry may not lock onto the incoming clock, which generates an erroneous clock within the device. The clock generated by the ClockLock and ClockBoost circuitry must also meet certain specifications. If the incoming clock meets these requirements during configuration, the APEX 20K ClockLock and ClockBoost circuitry will lock onto the clock during configuration. The circuit will be ready for use immediately after configuration. In APEX 20KE devices, the clock input standard is programmable, so the PLL cannot respond to the clock until the device is configured. The PLL locks onto the input clock as soon as configuration is complete. Figure 30 shows the incoming and generated clock specifications.

☞ For more information on ClockLock and ClockBoost circuitry, see *Application Note 115: Using the ClockLock and ClockBoost PLL Features in APEX Devices*.

Figure 32. APEX 20K AC Test Conditions *Note (1)*



Note to Figure 32:

(1) Power supply transients can affect AC measurements. Simultaneous transitions of multiple outputs should be avoided for accurate measurement. Threshold tests must not be performed under AC conditions. Large-amplitude, fast-ground-current transients normally occur as the device outputs discharge the load capacitances. When these transients flow through the parasitic inductance between the device ground pin and the test system ground, significant reductions in observable noise immunity can result.

Operating Conditions

Tables 23 through 26 provide information on absolute maximum ratings, recommended operating conditions, DC operating conditions, and capacitance for 2.5-V APEX 20K devices.

Table 23. APEX 20K 5.0-V Tolerant Device Absolute Maximum Ratings *Notes (1), (2)*

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage	With respect to ground *(3)*	–0.5	3.6	V
V_{CCIO}			–0.5	4.6	V
V_I	DC input voltage		–2.0	5.75	V
I_{OUT}	DC output current, per pin		–25	25	mA
T_{STG}	Storage temperature	No bias	–65	150	° C
T_{AMB}	Ambient temperature	Under bias	–65	135	° C
T_J	Junction temperature	PQFP, RQFP, TQFP, and BGA packages, under bias		135	° C
		Ceramic PGA packages, under bias		150	° C

Table 25. APEX 20K 5.0-V Tolerant Device DC Operating Conditions (Part 2 of 2) *Notes (2), (7), (8)*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{OL}	3.3-V low-level TTL output voltage	I_{OL} = 12 mA DC, V_{CCIO} = 3.00 V *(11)*			0.45	V
	3.3-V low-level CMOS output voltage	I_{OL} = 0.1 mA DC, V_{CCIO} = 3.00 V *(11)*			0.2	V
	3.3-V low-level PCI output voltage	I_{OL} = 1.5 mA DC, V_{CCIO} = 3.00 to 3.60 V *(11)*			0.1 × V_{CCIO}	V
	2.5-V low-level output voltage	I_{OL} = 0.1 mA DC, V_{CCIO} = 2.30 V *(11)*			0.2	V
		I_{OL} = 1 mA DC, V_{CCIO} = 2.30 V *(11)*			0.4	V
		I_{OL} = 2 mA DC, V_{CCIO} = 2.30 V *(11)*			0.7	V
I_I	Input pin leakage current	V_I = 5.75 to –0.5 V	–10		10	µA
I_{OZ}	Tri-stated I/O pin leakage current	V_O = 5.75 to –0.5 V	–10		10	µA
I_{CC0}	V_{CC} supply current (standby) (All ESBs in power-down mode)	V_I = ground, no load, no toggling inputs, -1 speed grade *(12)*		10		mA
		V_I = ground, no load, no toggling inputs, -2, -3 speed grades *(12)*		5		mA
R_{CONF}	Value of I/O pin pull-up resistor before and during configuration	V_{CCIO} = 3.0 V *(13)*	20		50	W
		V_{CCIO} = 2.375 V *(13)*	30		80	W

Table 29. APEX 20KE Device DC Operating Conditions *Notes (7), (8), (9)*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IH}	High-level LVTTL, CMOS, or 3.3-V PCI input voltage		1.7, 0.5 × V_{CCIO} *(10)*		4.1	V
V_{IL}	Low-level LVTTL, CMOS, or 3.3-V PCI input voltage		–0.5		0.8, 0.3 × V_{CCIO} *(10)*	V
V_{OH}	3.3-V high-level LVTTL output voltage	I_{OH} = –12 mA DC, V_{CCIO} = 3.00 V *(11)*	2.4			V
	3.3-V high-level LVCMOS output voltage	I_{OH} = –0.1 mA DC, V_{CCIO} = 3.00 V *(11)*	V_{CCIO} – 0.2			V
	3.3-V high-level PCI output voltage	I_{OH} = –0.5 mA DC, V_{CCIO} = 3.00 to 3.60 V *(11)*	0.9 × V_{CCIO}			V
	2.5-V high-level output voltage	I_{OH} = –0.1 mA DC, V_{CCIO} = 2.30 V *(11)*	2.1			V
		I_{OH} = –1 mA DC, V_{CCIO} = 2.30 V *(11)*	2.0			V
		I_{OH} = –2 mA DC, V_{CCIO} = 2.30 V *(11)*	1.7			V
V_{OL}	3.3-V low-level LVTTL output voltage	I_{OL} = 12 mA DC, V_{CCIO} = 3.00 V *(12)*			0.4	V
	3.3-V low-level LVCMOS output voltage	I_{OL} = 0.1 mA DC, V_{CCIO} = 3.00 V *(12)*			0.2	V
	3.3-V low-level PCI output voltage	I_{OL} = 1.5 mA DC, V_{CCIO} = 3.00 to 3.60 V *(12)*			0.1 × V_{CCIO}	V
	2.5-V low-level output voltage	I_{OL} = 0.1 mA DC, V_{CCIO} = 2.30 V *(12)*			0.2	V
		I_{OL} = 1 mA DC, V_{CCIO} = 2.30 V *(12)*			0.4	V
		I_{OL} = 2 mA DC, V_{CCIO} = 2.30 V *(12)*			0.7	V
I_I	Input pin leakage current	V_I = 4.1 to –0.5 V *(13)*	–10		10	µA
I_{OZ}	Tri-stated I/O pin leakage current	V_O = 4.1 to –0.5 V *(13)*	–10		10	µA
I_{CC0}	V_{CC} supply current (standby) (All ESBs in power-down mode)	V_I = ground, no load, no toggling inputs, -1 speed grade		10		mA
		V_I = ground, no load, no toggling inputs, -2, -3 speed grades		5		mA
R_{CONF}	Value of I/O pin pull-up resistor before and during configuration	V_{CCIO} = 3.0 V *(14)*	20		50	kΩ
		V_{CCIO} = 2.375 V *(14)*	30		80	kΩ
		V_{CCIO} = 1.71 V *(14)*	60		150	kΩ

Figure 33. Relationship between V_{CCIO} & V_{CCINT} for 3.3-V PCI Compliance

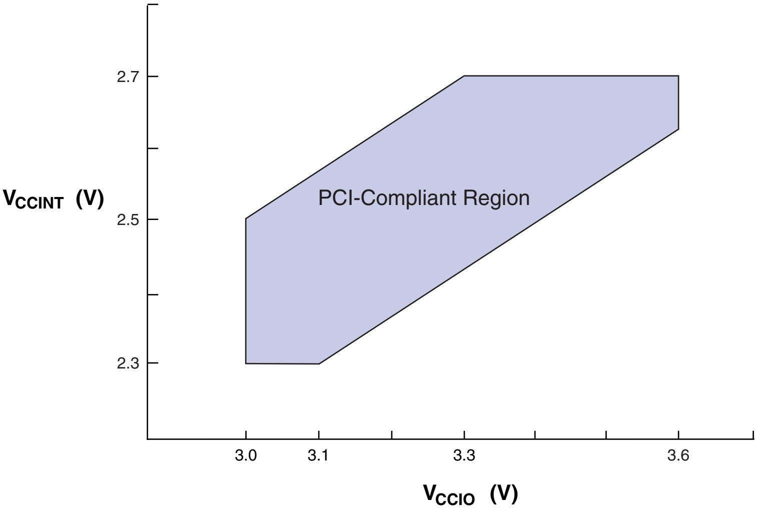
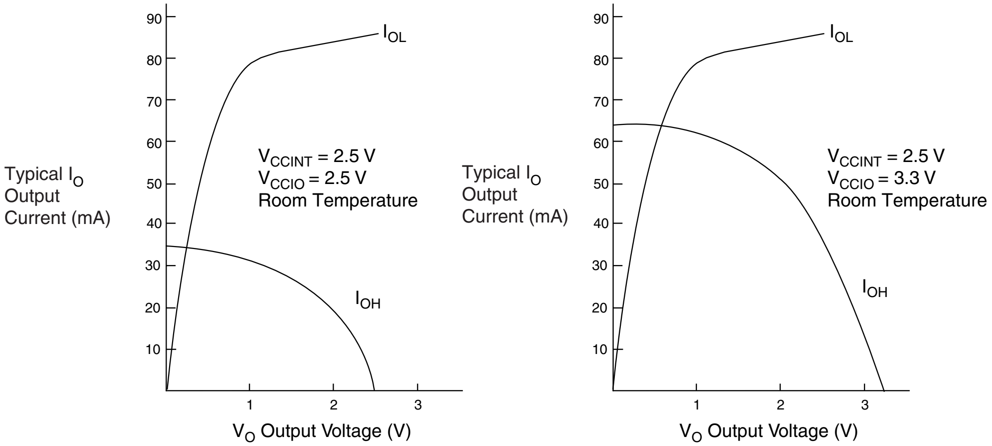


Figure 34 shows the typical output drive characteristics of APEX 20K devices with 3.3-V and 2.5-V V_{CCIO}. The output driver is compatible with the 3.3-V ***PCI Local Bus Specification, Revision 2.2*** (when `VCCIO` pins are connected to 3.3 V). 5-V tolerant APEX 20K devices in the -1 speed grade are 5-V PCI compliant over all operating conditions.

Figure 34. Output Drive Characteristics of APEX 20K Device *Note (1)*



Note to Figure 34:

(1) These are transient (AC) currents.

All specifications are always representative of worst-case supply voltage and junction temperature conditions. All output-pin-timing specifications are reported for maximum driver strength.

Figure 36 shows the f_{MAX} timing model for APEX 20K devices.

Figure 36. APEX 20K f_{MAX} Timing Model

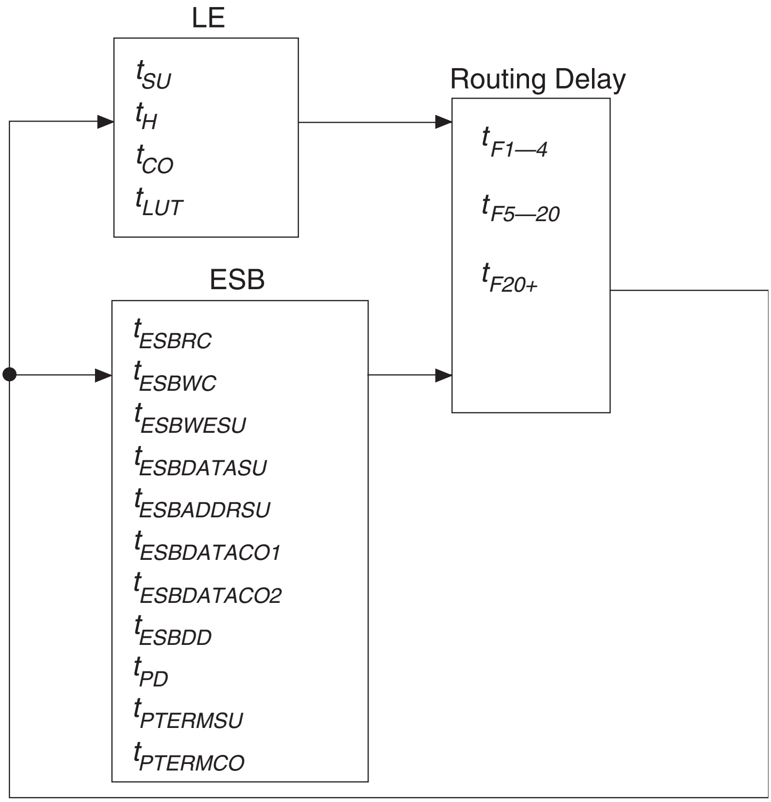


Figure 37 shows the f_{MAX} timing model for APEX 20KE devices. These parameters can be used to estimate f_{MAX} for multiple levels of logic. Quartus II software timing analysis should be used for more accurate timing information.

Note to Tables 32 and 33:

(1) These timing parameters are sample-tested only.

Tables 34 through 37 show APEX 20KE LE, ESB, routing, and functional timing microparameters for the f_{MAX} timing model.

Table 34. APEX 20KE LE Timing Microparameters

Symbol	Parameter
t_{SU}	LE register setup time before clock
t_{H}	LE register hold time after clock
t_{CO}	LE register clock-to-output delay
t_{LUT}	LUT delay for data-in to data-out

Table 35. APEX 20KE ESB Timing Microparameters

Symbol	Parameter
t_{ESBARC}	ESB Asynchronous read cycle time
t_{ESBSRC}	ESB Synchronous read cycle time
t_{ESBAWC}	ESB Asynchronous write cycle time
t_{ESBSWC}	ESB Synchronous write cycle time
$t_{ESBWASU}$	ESB write address setup time with respect to WE
t_{ESBWAH}	ESB write address hold time with respect to WE
$t_{ESBWDSU}$	ESB data setup time with respect to WE
t_{ESBWDH}	ESB data hold time with respect to WE
$t_{ESBRASU}$	ESB read address setup time with respect to RE
t_{ESBRAH}	ESB read address hold time with respect to RE
$t_{ESBWESU}$	ESB WE setup time before clock when using input register
t_{ESBWEH}	ESB WE hold time after clock when using input register
$t_{ESBDATASU}$	ESB data setup time before clock when using input register
$t_{ESBDATAH}$	ESB data hold time after clock when using input register
$t_{ESBWADDRSU}$	ESB write address setup time before clock when using input registers
$t_{ESBRADDRSU}$	ESB read address setup time before clock when using input registers
$t_{ESBDATACO1}$	ESB clock-to-output delay when using output registers
$t_{ESBDATACO2}$	ESB clock-to-output delay without output registers
t_{ESBDD}	ESB data-in to data-out delay for RAM mode
t_{PD}	ESB Macrocell input to non-registered output
$t_{PTERMSU}$	ESB Macrocell register setup time before clock
$t_{PTERMCO}$	ESB Macrocell register clock-to-output delay

Table 36. APEX 20KE Routing Timing Microparameters *Note (1)*

Symbol	Parameter
t_{F1-4}	Fanout delay using Local Interconnect
t_{F5-20}	Fanout delay estimate using MegaLab Interconnect
t_{F20+}	Fanout delay estimate using FastTrack Interconnect

Note to Table 36:

(1) These parameters are worst-case values for typical applications. Post-compilation timing simulation and timing analysis are required to determine actual worst-case performance.

Table 37. APEX 20KE Functional Timing Microparameters

Symbol	Parameter
TCH	Minimum clock high time from clock pin
TCL	Minimum clock low time from clock pin
TCLRP	LE clear Pulse Width
TPREP	LE preset pulse width
TESBCH	Clock high time for ESB
TESBCL	Clock low time for ESB
TESBWP	Write pulse width
TESBRP	Read pulse width

Tables 38 and 39 describe the APEX 20KE external timing parameters.

Table 38. APEX 20KE External Timing Parameters *Note (1)*

Symbol	Clock Parameter	Conditions
t_{INSU}	Setup time with global clock at IOE input register	
t_{INH}	Hold time with global clock at IOE input register	
t_{OUTCO}	Clock-to-output delay with global clock at IOE output register	C1 = 10 pF
$t_{INSUPLL}$	Setup time with PLL clock at IOE input register	
t_{INHPLL}	Hold time with PLL clock at IOE input register	
$t_{OUTCOPLL}$	Clock-to-output delay with PLL clock at IOE output register	C1 = 10 pF

Table 60. EP20K60E External Bidirectional Timing Parameters							
Symbol	**-1**		**-2**		**-3**		**Unit**
	Min	**Max**	**Min**	**Max**	**Min**	**Max**	
$t_{INSUBIDIR}$	2.77		2.91		3.11		ns
$t_{INHBIDIR}$	0.00		0.00		0.00		ns
$t_{OUTCOBIDIR}$	2.00	4.84	2.00	5.31	2.00	5.81	ns
$t_{XZBIDIR}$		6.47		7.44		8.65	ns
$t_{ZXBIDIR}$		6.47		7.44		8.65	ns
$t_{INSUBIDIRPLL}$	3.44		3.24		-		ns
$t_{INHBIDIRPLL}$	0.00		0.00		-		ns
$t_{OUTCOBIDIRPLL}$	0.50	3.37	0.50	3.69	-	-	ns
$t_{XZBIDIRPLL}$		5.00		5.82		-	ns
$t_{ZXBIDIRPLL}$		5.00		5.82		-	ns

Tables 61 through 66 describe f_{MAX} LE Timing Microparameters, f_{MAX} ESB Timing Microparameters, f_{MAX} Routing Delays, Minimum Pulse Width Timing Parameters, External Timing Parameters, and External Bidirectional Timing Parameters for EP20K100E APEX 20KE devices.

Table 61. EP20K100E f_{MAX} LE Timing Microparameters							
Symbol	**-1**		**-2**		**-3**		**Unit**
	Min	**Max**	**Min**	**Max**	**Min**	**Max**	
t_{SU}	0.25		0.25		0.25		ns
t_{H}	0.25		0.25		0.25		ns
t_{CO}		0.28		0.28		0.34	ns
t_{LUT}		0.80		0.95		1.13	ns

Table 69. EP20K160E f_{MAX} Routing Delays

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{F1-4}		0.25		0.26		0.28	ns
t_{F5-20}		1.00		1.18		1.35	ns
t_{F20+}		1.95		2.19		2.30	ns

Table 70. EP20K160E Minimum Pulse Width Timing Parameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{CH}	1.34		1.43		1.55		ns
t_{CL}	1.34		1.43		1.55		ns
t_{CLRP}	0.18		0.19		0.21		ns
t_{PREP}	0.18		0.19		0.21		ns
t_{ESBCH}	1.34		1.43		1.55		ns
t_{ESBCL}	1.34		1.43		1.55		ns
t_{ESBWP}	1.15		1.45		1.73		ns
t_{ESBRP}	0.93		1.15		1.38		ns

Table 71. EP20K160E External Timing Parameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.23		2.34		2.47		ns
t_{INH}	0.00		0.00		0.00		ns
t_{OUTCO}	2.00	5.07	2.00	5.59	2.00	6.13	ns
$t_{INSUPLL}$	2.12		2.07		-		ns
t_{INHPLL}	0.00		0.00		-		ns
$t_{OUTCOPLL}$	0.50	3.00	0.50	3.35	-	-	ns

Table 74. EP20K200E f_{MAX} ESB Timing Microparameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{ESBARC}		1.68		2.06		2.24	ns
t_{ESBSRC}		2.27		2.77		3.18	ns
t_{ESBAWC}		3.10		3.86		4.50	ns
t_{ESBSWC}		2.90		3.67		4.21	ns
$t_{ESBWASU}$	0.55		0.67		0.74		ns
t_{ESBWAH}	0.36		0.46		0.48		ns
$t_{ESBWDSU}$	0.69		0.83		0.95		ns
t_{ESBWDH}	0.36		0.46		0.48		ns
$t_{ESBRASU}$	1.61		1.90		2.09		ns
t_{ESBRAH}	0.00		0.00		0.01		ns
$t_{ESBWESU}$	1.42		1.71		2.01		ns
t_{ESBWEH}	0.00		0.00		0.00		ns
$t_{ESBDATASU}$	-0.06		-0.07		0.05		ns
$t_{ESBDATAH}$	0.13		0.13		0.13		ns
$t_{ESBWADDRSU}$	0.11		0.13		0.31		ns
$t_{ESBRADDRSU}$	0.18		0.23		0.39		ns
$t_{ESBDATACO1}$		1.09		1.35		1.51	ns
$t_{ESBDATACO2}$		2.19		2.75		3.22	ns
t_{ESBDD}		2.75		3.41		4.03	ns
t_{PD}		1.58		1.97		2.33	ns
$t_{PTERMSU}$	1.00		1.22		1.51		ns
$t_{PTERMCO}$		1.10		1.37		1.09	ns

Table 75. EP20K200E f_{MAX} Routing Delays

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{F1-4}		0.25		0.27		0.29	ns
t_{F5-20}		1.02		1.20		1.41	ns
t_{F20+}		1.99		2.23		2.53	ns

Table 78. EP20K200E External Bidirectional Timing Parameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	2.81		3.19		3.54		ns
$t_{INHBIDIR}$	0.00		0.00		0.00		ns
$t_{OUTCOBIDIR}$	2.00	5.12	2.00	5.62	2.00	6.11	ns
$t_{XZBIDIR}$		7.51		8.32		8.67	ns
$t_{ZXBIDIR}$		7.51		8.32		8.67	ns
$t_{INSUBIDIRPLL}$	3.30		3.64		-		ns
$t_{INHBIDIRPLL}$	0.00		0.00		-		ns
$t_{OUTCOBIDIRPLL}$	0.50	3.01	0.50	3.36	-	-	ns
$t_{XZBIDIRPLL}$		5.40		6.05		-	ns
$t_{ZXBIDIRPLL}$		5.40		6.05		-	ns

Tables 79 through 84 describe f_{MAX} LE Timing Microparameters, f_{MAX} ESB Timing Microparameters, f_{MAX} Routing Delays, Minimum Pulse Width Timing Parameters, External Timing Parameters, and External Bidirectional Timing Parameters for EP20K300E APEX 20KE devices.

Table 79. EP20K300E f_{MAX} LE Timing Microparameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.16		0.17		0.18		ns
t_H	0.31		0.33		0.38		ns
t_{CO}		0.28		0.38		0.51	ns
t_{LUT}		0.79		1.07		1.43	ns

Table 80. EP20K300E f_{MAX} ESB Timing Microparameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{ESBARC}		1.79		2.44		3.25	ns
t_{ESBSRC}		2.40		3.12		4.01	ns
t_{ESBAWC}		3.41		4.65		6.20	ns
t_{ESBSWC}		3.68		4.68		5.93	ns
$t_{ESBWASU}$	1.55		2.12		2.83		ns
t_{ESBWAH}	0.00		0.00		0.00		ns
$t_{ESBWDSU}$	1.71		2.33		3.11		ns
t_{ESBWDH}	0.00		0.00		0.00		ns
$t_{ESBRASU}$	1.72		2.34		3.13		ns
t_{ESBRAH}	0.00		0.00		0.00		ns
$t_{ESBWESU}$	1.63		2.36		3.28		ns
t_{ESBWEH}	0.00		0.00		0.00		ns
$t_{ESBDATASU}$	0.07		0.39		0.80		ns
$t_{ESBDATAH}$	0.13		0.13		0.13		ns
$t_{ESBWADDRSU}$	0.27		0.67		1.17		ns
$t_{ESBRADDRSU}$	0.34		0.75		1.28		ns
$t_{ESBDATACO1}$		1.03		1.20		1.40	ns
$t_{ESBDATACO2}$		2.33		3.18		4.24	ns
t_{ESBDD}		3.41		4.65		6.20	ns
t_{PD}		1.68		2.29		3.06	ns
$t_{PTERMSU}$	0.96		1.48		2.14		ns
$t_{PTERMCO}$		1.05		1.22		1.42	ns

Table 81. EP20K300E f_{MAX} Routing Delays

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{F1-4}		0.22		0.24		0.26	ns
t_{F5-20}		1.33		1.43		1.58	ns
t_{F20+}		3.63		3.93		4.35	ns